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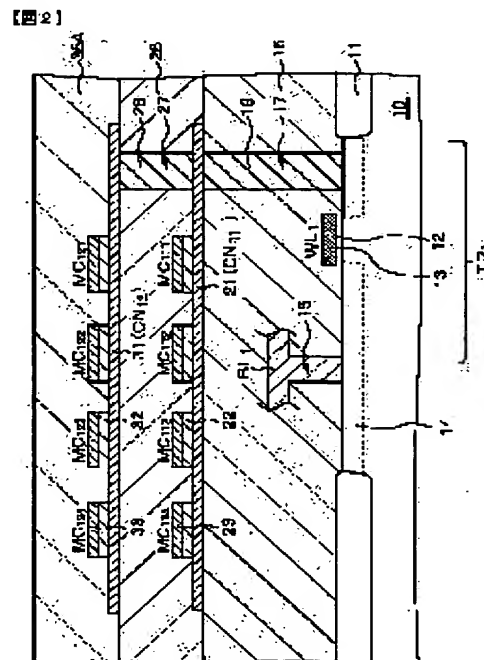
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(54) FERROELECTRIC TYPE NON-VOLATILE SEMICONDUCTOR MEMORY, AND ITS DRIVING METHOD

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a ferroelectric type non-volatile semiconductor memory in which capacity can be made larger without being restricted by minimum machining size and further high integration is realized.

SOLUTION: A ferroelectric type non-volatile semiconductor memory comprises (A) bit lines BL1 (B) a transistor TR1 for selection, (C) memory units MU1N of N pieces ($N \geq 2$) constituted respectively of memory cells MC1NM of M pieces ($M \geq 2$), and (D) plate lines PLm of M \times N lines, the memory units MU1N of N pieces are laminated through inter-layer insulator layers 26.



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